

PI3L301D

3.3V, 16-Bit to 8-Bit, Mux/DeMux Gigabit Ethernet LAN Switch with Single Enable

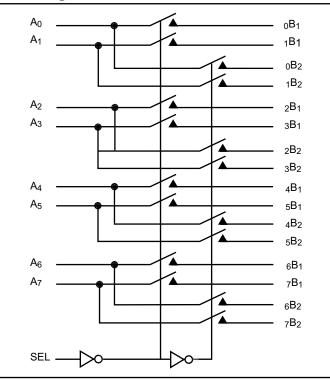
Features

- R_{ON} is 4Ω typical
- Low bit-to-bit skew: 200ps
- Low crosstalk: -27dB @ 250MHz
- Low Current Consumption: 20µA
- Near-Zero propagation delay: 250ps
- Switching speed: 9ns
- Channel On-Capacitance: 9.5pF (typical)
- V_{CC} Operating Range: +3.0V to +3.6V
- ESD >3000V . . . Human Body Model
- >350 MHz bandwidth (or data frequency)
- Packaging (Pb-free & Green available): 48-pin 240 mil wide plastic TSSOP (A)

Applications

- Dual Physical Layer Device sharing to one interface connector
- SONET OC-12(622Mbps) signal routing
- Routes physical layer signals for 10/100/1000 Mbit Ethernet

Block Diagram



Description

Pericom Semiconductor's PI3L series of logic circuits are produced using the Company's advanced sub-micron CMOS technology, achieving industry leading performance.

The PI3L301D is a 16- to 8-bit multiplexer/demultiplexer LAN Switch. Industry leading advantages include a propagation delay of less than 250ps, resulting from its low channel resistance and I/O capacitance. The device multiplexes differential outputs from a Gigabit Ethernet transceiver (PHY) device to one of two corresponding B1 or B2 outputs. The switch is bidirectional and offers little or no attenuation of the high-speed signals at the outputs. It is designed for low bit-to-bit skew, high channel-to-channel noise isolation and is compatible with various standards, such as 10/100/ 1000 Base-T (Ethernet).

Generally, this part can be used to replace mechanical relays in low-voltage LAN applications that interface a physical layer over CAT 5 or CAT 6 unshielded twisted pair cable through an isolation transformer.

Pin Description

- eser peron			
			 1
Vdd 🕻	1	48	□ 0 ^B 1
A0 [2		□ 1 ^B 1
GND [3	46	GND
Α1 [4	45	□ 0B2
gnd [5	44	□ 1B2
V _{DD} [6	43] GND
GND [7	42	□ 2B1
A ₂ [8	41	∃ 3B1
gnd [9	40] GND
A3 [10	39] 2B2
gnd [11	38	3 B2
V _{DD} [12	37	GND
GND [13	36	
NC [14	35	J 4B1
A4 [15	34	□ ₅ B ₁
GND [16		GND GND
A5 [17	32	□ ₄ B ₂
GND [18		□ ₅ B ₂
Vdd [19		GND
GND C	20		□ ₆ B ₁
A6 🛛	21		□ ₇ B ₁
GND	22		
A7	23	26	1 ₆ B ₂
SEL C	24	25	□ _{7B2}
I			



Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

Storage Temperature	65°C to +150°C
Supply Voltage to Ground Potential	0.5V to +4.0V
DC Input Voltage	0.5V to +5.5V
DC Output Current	120mA
Power Dissipation	0.5W

Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Truth Table

Function	SEL
A _N to _N B ₁	L
A_N to $_NB_2$	Н

Units

V

μA

Ω

DC Electrical Characteristics for 1000 Base-T Ethernet Switching over Operating Range

 $(T_A = -40^{\circ}C \text{ to } +85^{\circ}C, V_{CC} = 3.3V \pm 10\%)$ Test Conditions⁽¹⁾ Typ.⁽²⁾ Paramenter Description Min. Max. 2 VIH Input HIGH Voltage Guaranteed HIGH level _ VIL Input LOW Voltage Guaranteed LOW level -0.5 0.8 -VIK $V_{CC} = Max., I_{IN} = -18mA$ -0.7-1.2Clamp Diode Voltage _ $V_{CC} = Max., V_{IN} = V_{CC}$ Input HIGH Current ±5 I_{IH} _ _ $V_{CC} = Max., V_{IN} = GND$ ±5 IIL Input LOW Current _ _ Power Down Leakage Current $V_{CC} = 0V, V_A = 0V, V_B \le 3.6$ ±5 IOFF -- $V_{CC} = Min., 1.5V \le V_{IN} \le V_{CC},$ Switch On-Resistance⁽³⁾ 4 8 RON $I_{IN} = -40 \text{mA}$ V_{CC} = Min., V_{IN} @ 1.5V and V_{CC} , On-Resistance Flatness⁽⁴⁾ 1 R_{FLAT(ON)} _ $I_{IN} = -40 \text{mA}$ On-Resistance match from center $V_{CC} = Min., 1.5V \le V_{IN} \le V_{CC},$ 0.9 2 ΔR_{ON} ports to any other $port^{(4)}$ $I_{IN} = -40 \text{mA}$

DC Electrical Characteristics for 10/100 Base-T Ethernet Switching over Operating Range

 $(T_A = -40^{\circ}C \text{ to } +85^{\circ}C, V_{CC} = 3.3V \pm 10\%)$

Paramenter	Description	Test Conditions ⁽¹⁾	Min.	Typ. ⁽²⁾	Max.	Units
V _{IH}	Input HIGH Voltage	Guaranteed HIGH level	2.0	-	-	
V _{IL}	Input LOW Voltage	Guaranteed LOW level	-0.5	-	0.8	V
V _{IK}	Clamp Diode Voltage	$V_{CC} = Max., I_{IN} = -18mA$	-	-0.7	-1.2	
I _{IH}	Input HIGH Current	$V_{CC} = Max., V_{IN} = V_{CC}$	-	-	±5	
I _{IL}	Input LOW Current	$V_{CC} = Max., V_{IN} = GND$	-	-	±5	μΑ
I _{OFF}	Power Down Leakage Current	$V_{CC} = 0V, V_A = 0V, V_B \le 3.6$	-	-	±5	
R _{ON}	Switch On-Resistance ⁽³⁾	$\label{eq:VCC} \begin{split} V_{CC} &= Min., \ 1.25V \leq V_{IN} \leq V_{CC}, \\ I_{IN} &= -10mA \ to - 30mA \end{split}$	-	-	8	
R _{FLAT(ON)}	On-Resistance Flatness ⁽⁴⁾	V_{CC} = Min., V_{IN} @ 1.25V and V_{CC} , I_{IN} = -10mA to -30mA	-	1.0	-	Ω
ΔR _{ON}	On-Resistance match from center ports to any other port ⁽⁴⁾	$\label{eq:VCC} \begin{array}{l} V_{CC} = Min., \ 1.25V \leq V_{IN} \leq V_{CC}, \\ I_{IN} = -10mA \ to -30mA \end{array}$	-	0.9	2.0	

Capacitance ($T_A = 25^{\circ}C$, f = 1MHz)

Parameters ⁽⁴⁾	Description	Test Conditions	Тур.	Max.	Units
C _{IN}	Input Capacitance		3.1	3.6	
C _{OFF(B1, B2)}	Port B Capacitance, Switch OFF	$V_{IN} = 0V$	2.8	6.0	pF
C _{ON(A/B)}	A/B Capacitance, Switch ON		9.5 ⁽⁵⁾	10.9	

Notes:

1. For max. or min. conditions, use appropriate value specified under Electrical Characteristics for the applicable device type.

2. Typical values are at $V_{CC} = 3.3V$, $T_A = 25^{\circ}C$ ambient and maximum loading.

3. Measured by the voltage drop between A and B pins at indicated current through the switch. On-Resistance is determined by the lower of the voltages on the two (A & B) pins.

4. This parameter is determined by device characterization but is not production tested.

5. Measured on worst case corner pin.



Power Supply Characteristics

Parameters	Description	Test Conditions ⁽¹⁾	Min.	Typ. ⁽²⁾	Max.	Units
I _{CC}	Quiescent Power Supply Current	V_{CC} = Max., V_{IN} = GND or V_{CC}	-	-	800	μA

Notes:

1. For max. or min. conditions, use appropriate value specified under Electrical Characteristics for the applicable device type.

2. Typical values are at $V_{CC} = 3.3V$, $T_A = 25^{\circ}C$ ambient and maximum loading.

Dynamic Electrical Characteristics Over the Operating Range (T_A=-40° to +85°C, V_{CC}=3.3V±10%, GND=0V)

Parameter	Description	Test Conditions ⁽¹⁾	Min.	Typ. ⁽²⁾	Max.	Units
X _{TALK}	Crosstalk	f = 250MHz, See Fig. 2	-	-27	-	dB
O _{IRR}	OFF Isolation	f = 250MHz, See Fig. 3	-	-32	-	aв
BW	Bandwidth –3dB	$C_L = 10 pf$, See Fig. 1	-	350	-	MHz

Switching Characteristics

Paramenter	Description	Test Conditions	Min.	Typ. ⁽²⁾	Max.	Units
tPD	Propagation Delay(3,4)		-	0.25		
t _{PZH} , t _{PZL}	Line Enable Time - SEL to A _N , B _N		0.5	-	15	
t _{PHZ} , t _{PLZ}	Line Disable Time - SEL to A _N , B _N		0.5	-	9	ns
t _{SK(0)}	Output Skew between center port (A4 to A5) to any other $port(4)$		-	0.1	0.2	115
t _{SK(p)}	Skew between opposite transitions of the same output $(t_{PHL} - t_{PLH})$ (4)		-	0.1	0.2	

Notes:

1. For max. or min. conditions, use appropriate value specified under Electrical Characteristics for the applicable device type.

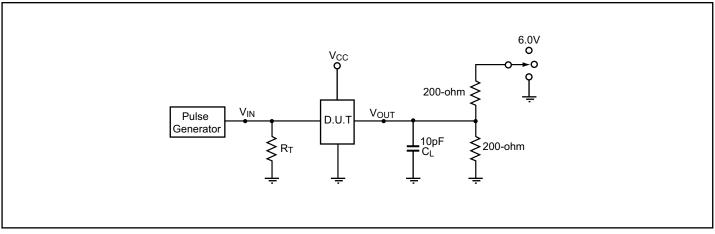
2. Typical valves are at Vcc = 3.3V, $Ta = 25^{\circ}C$ ambient and maximum loading.

3. The bus switch contributes no propagational delay other than the RC delay of the On-Resistance of the switch and the load capacitance. The time constant for the switch alone is of the order of 0.25ns for 10pF load. Since this time constant is much smaller than the rise/fall times of typical driving signals, it adds very little propagational delay to the system. Propagational delay of the bus switch when used in a system is determined by the driving circuit on the driving side of the switch and its interactions with the load on the driven side.

4. Guaranteed by design.



Test Circuit for Electrical Characteristics



Notes:

 C_L = Load capacitance: includes jig and probe capacitance.

 R_T = Termination resistance: should be equal to Z_{OUT} of the Pulse Generator

All input impulses are supplied by generators having the following characteristics: f = 10MHz, $Z_0 = 50\Omega$, $t_R \le 2.5ns$, $t_F \le 2.5ns$. The outputs are measured one at a time with one transition per measurement.

Switch Positions

Test	Switch
t _{PLZ} , t _{PZL} (output on B-side)	6.0V
t _{PHZ} , t _{PZH} (output on B-side)	GND
Prop Delay	Open

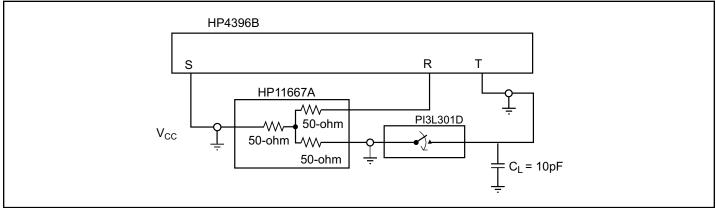


Figure 1. Bandwidth -3db Testing



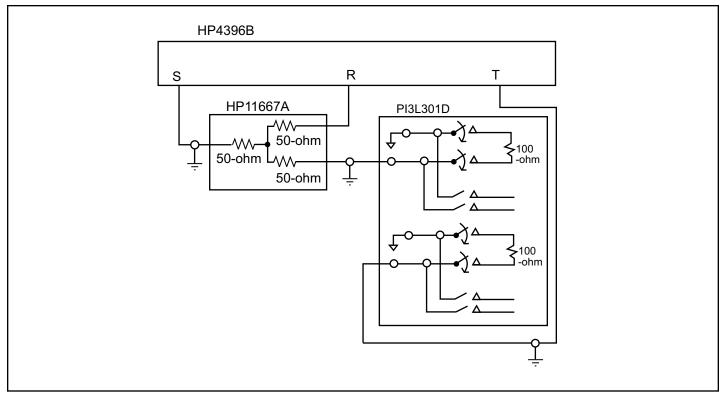


Figure 2. Crosstalk Test Setup

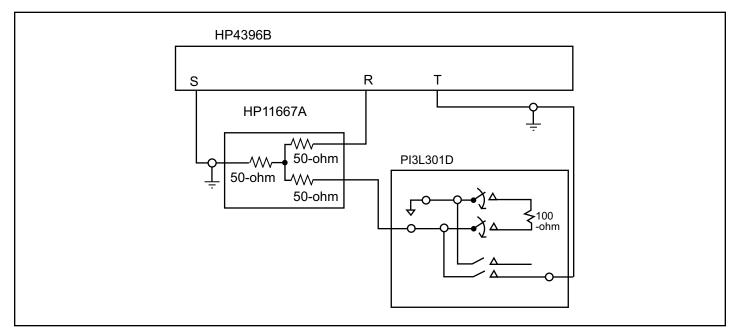
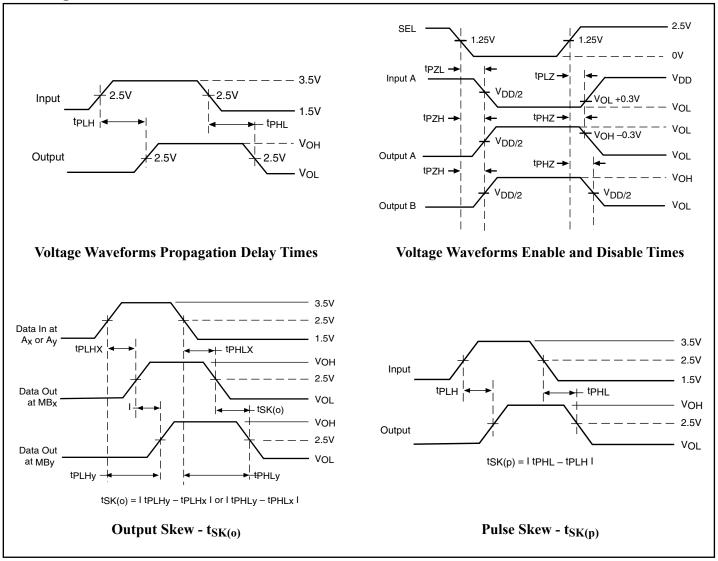


Figure 3 . Off Isolation Tets Setup



Switching Waveforms



Applications Information

Logic Inputs

The logic control inputs can be driven up to +3.6V regardless of the supply voltage. For example, given a +3.3V supply, the output enables or select pins may be driven low to 0V and high to 3.6V. Driving IN Rail-to-Rail® minimizes power consumption.

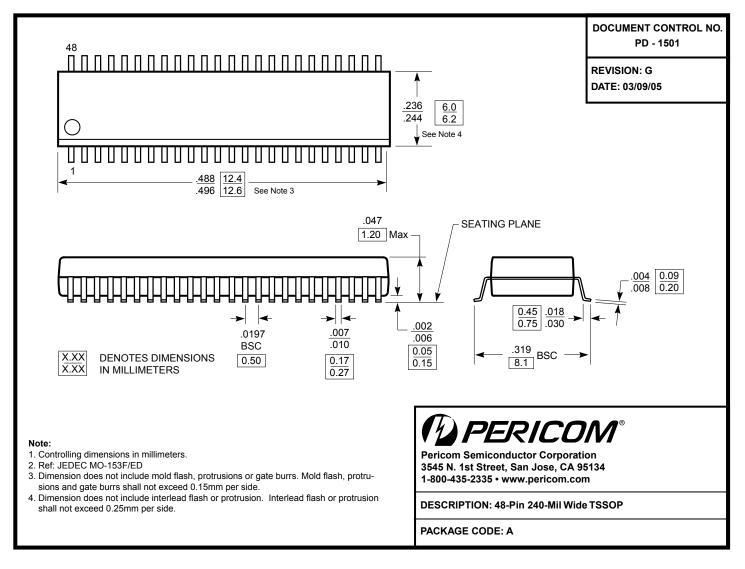
Power-Supply Sequencing

Proper power-supply sequencing is advised for all CMOS devices. It is recommended to always apply V_{CC} before applying signals to the input/output or control pins.

Rail-to-Rail is a registered trademark of Nippon Motorola, Ltd



Packaging Mechanical: 48-Pin TSSOP (A)



Ordering Information

Ordering Code	Package Code	Package Description
PI3L301DAE	А	Pb-free & Green, 48-pin 240 mil wide plastic TSSOP

Notes:

- Thermal characteristics can be found on the company web site at www.pericom.com/packaging/
- E = Pb-free & Green
- Adding an X suffix = Tape/Reel

单击下面可查看定价,库存,交付和生命周期等信息

>>Diodes Incorporated(达迩科技(美台))